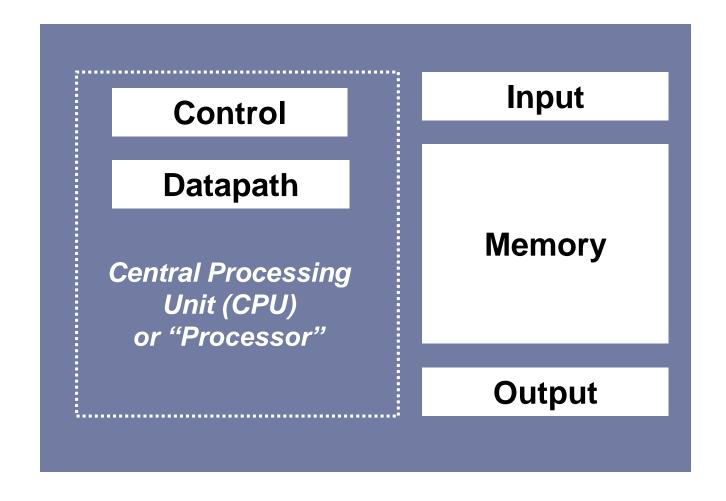
# Lecture 6 - Modeling of Memory and Register Files

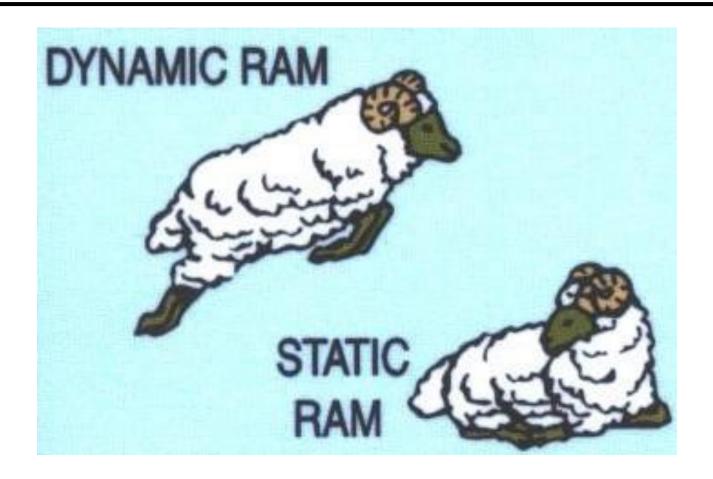
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### A typical Computing System



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### Types of Computer Memories

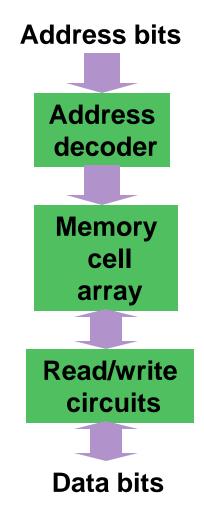


#### From the cover of:

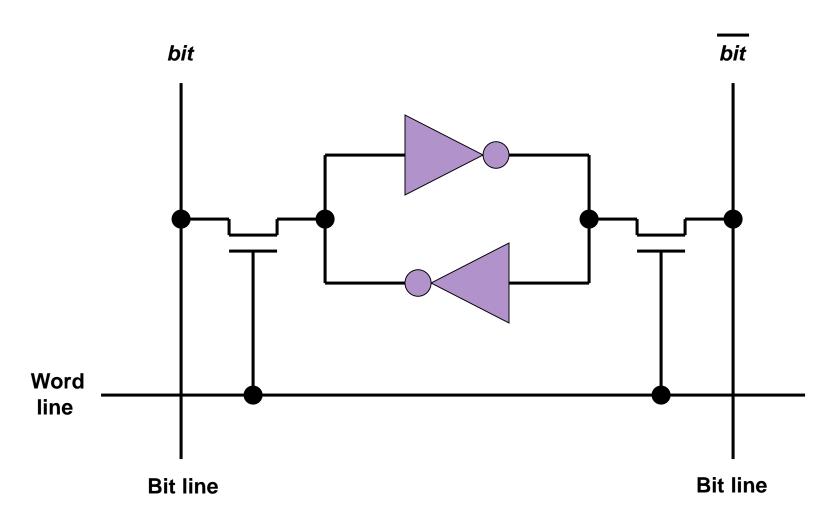
A. S. Tanenbaum, *Structured Computer Organization, Fifth Edition*, Upper Saddle River, New Jersey: Pearson Prentice Hall, 2006.

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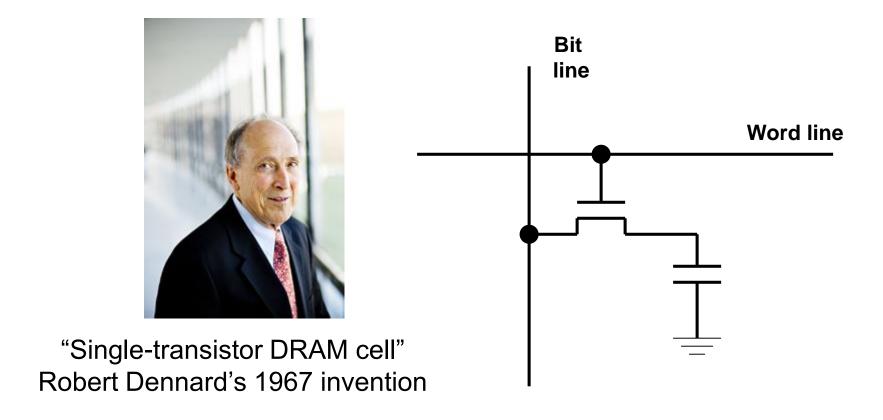
### Random Access Memory (RAM)



#### Six-Transistor SRAM Cell



### Dynamic RAM (DRAM) Cell



### **Electronic Memory Devices**

Memory technology	Typical access time	\$ per GiB in 2012
SRAM semiconductor memory	0.5–2.5 ns	\$500-\$1000
DRAM semiconductor memory	50–70 ns	\$10–\$20
Flash semiconductor memory	5,000–50,000 ns	\$0.75–\$1.00
Magnetic disk	5,000,000— 20,000,000 ns	\$0.05-\$0.10

#### For more on memories:

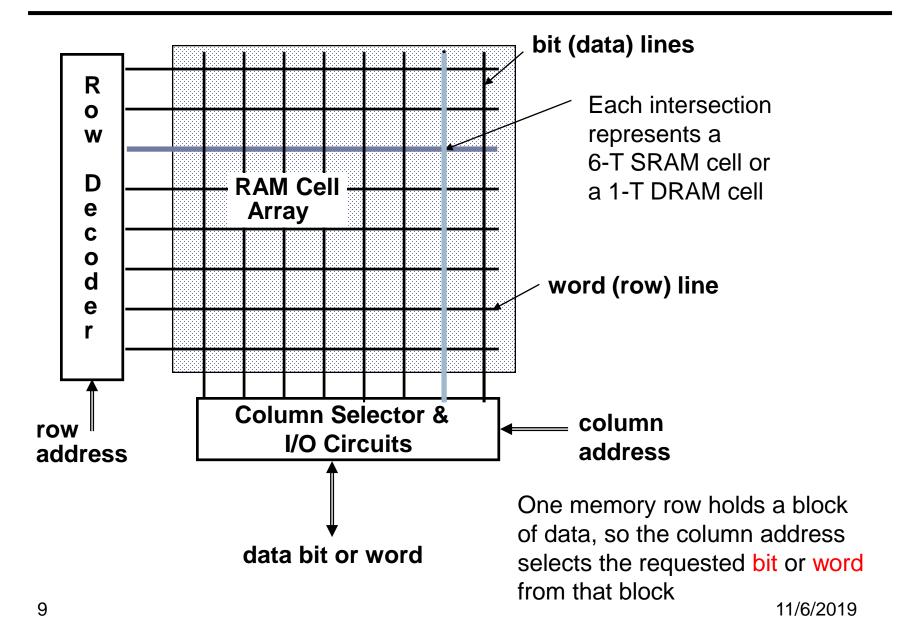
Semiconductor Memories: A Handbook of Design, Manufacture and Application, by Betty Prince, Wiley 1996.

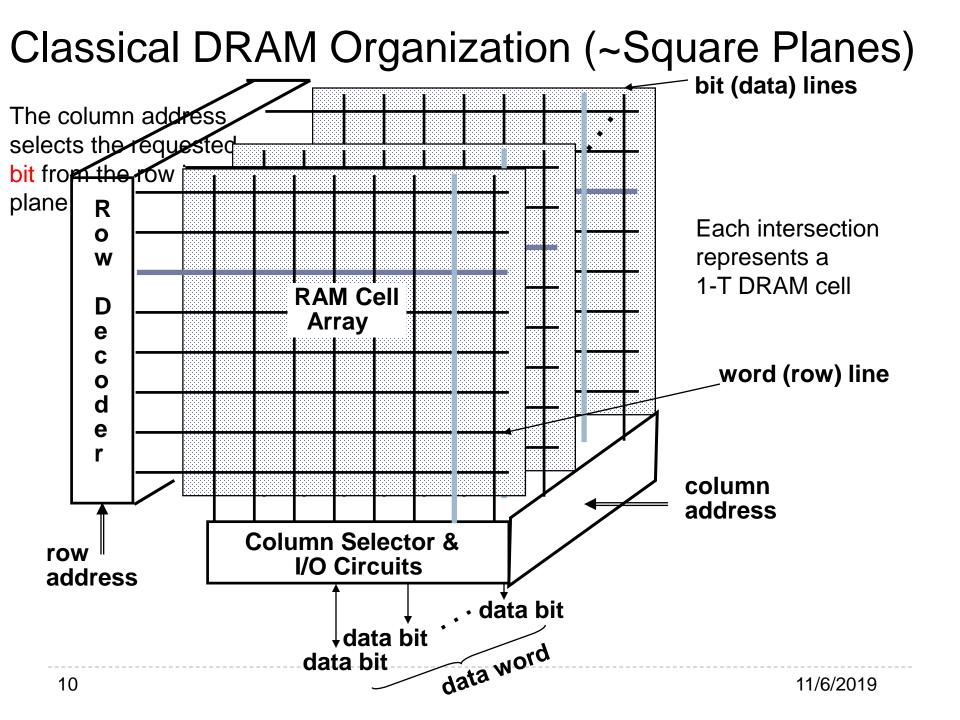
*Emerging Memories: Technologies and Trends*, by Betty Prince, Springer 2002.

### **DRAM** Evolution

Year introduced	Chip size	\$ per GiB	Total access time to a new row/column	Average column access time to existing row
1980	64 KiB	\$1,500,000	250 ns	150 ns
1983	256 KiB	\$500,000	185 ns	100 ns
1985	1 MeB	\$200,000	135 ns	40 ns
1989	4 MeB	\$50,000	110 ns	40 ns
1992	16 MeB	\$15,000	90 ns	30 ns
1996	64 MeB	\$10,000	60 ns	12 ns
1998	128 MeB	\$4,000	60 ns	10 ns
2000	256 MeB	\$1,000	55 ns	7 ns
2004	512 MeB	\$250	50 ns	5 ns
2007	1 GiB	\$50	45 ns	1.25 ns
2010	2 GiB	\$30	40 ns	1 ns
2012	4 GiB	\$1	35 ns	0.8 ns

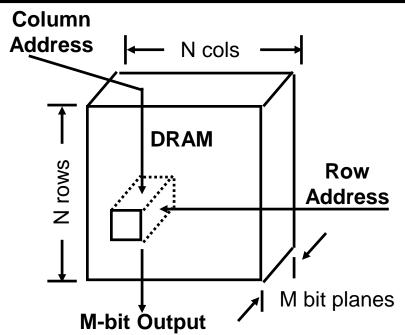
### Classical RAM Organization (~Square)

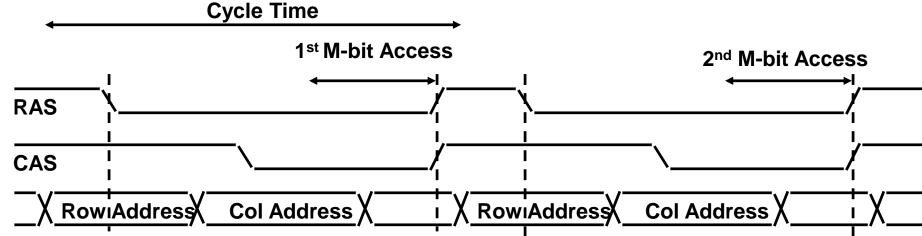




#### Classical DRAM Operation

- DRAM Organization:
  - N rows x N column x M-bit
  - Read or Write M-bit at a time
  - Each M-bit access requires a RAS / CAS cycle





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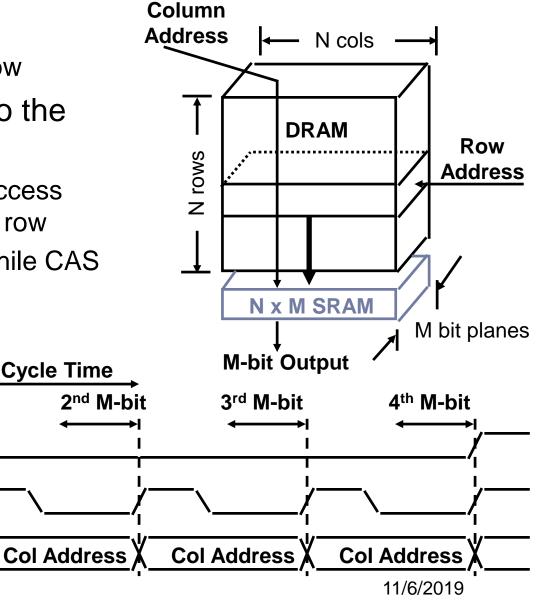
#### Page Mode DRAM Operation

- Page Mode DRAM
  - N x M SRAM to save a row
- After a row is read into the SRAM "register"
  - Only CAS is needed to access other M-bit words on that row
  - RAS remains asserted while CAS is toggled

1<sup>st</sup> M-bit Access

Col Address X

**Cycle Time** 



12

RowiAddress

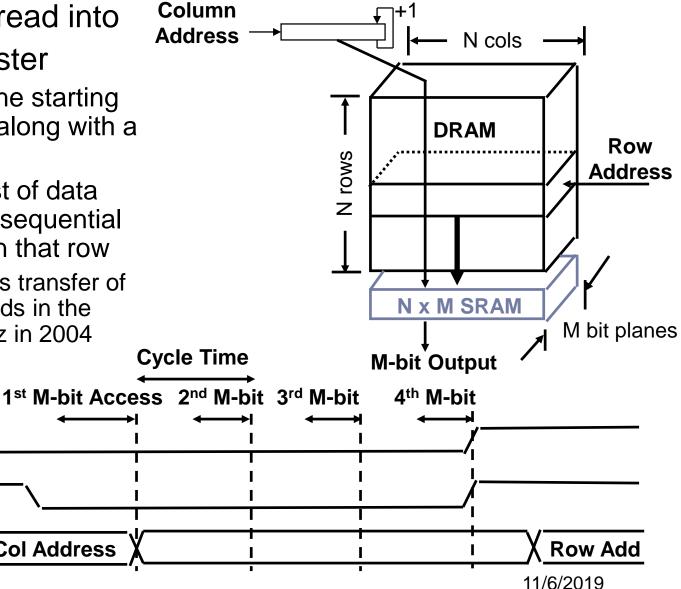
**RAS** 

CAS

# Synchronous DRAM (SDRAM) Operation

- After a row is read into the SRAM register
  - Inputs CAS as the starting "burst" address along with a burst length
  - Transfers a burst of data from a series of sequential addresses within that row
    - A clock controls transfer of successive words in the burst – 300MHz in 2004

XRow Address X Col Address



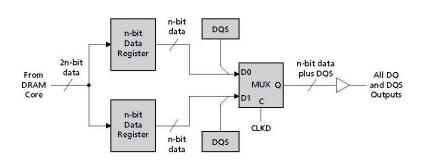
**RAS** 

CAS

#### Other SDRAM Architectures

#### Double Data Rate SDRAMs – DDR-SDRAMs

- Double data rate because they transfer data on both the rising and falling edge of the clock
  - ➤ Most widely used form of SDRAMs
- For DDR memory, 2n prefetch architecture means
  - Internal bus width is twice of external bus width
  - > Hence, internal column access freq can be half of external data rate
- For users, 2n prefetch means that data access occurs in pairs
  - ➤ A single READ fetches two data words
  - ➤ A single WRITE, two data words must be provided



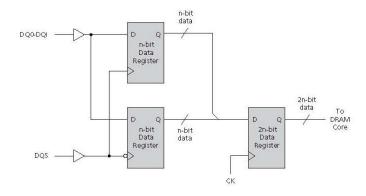
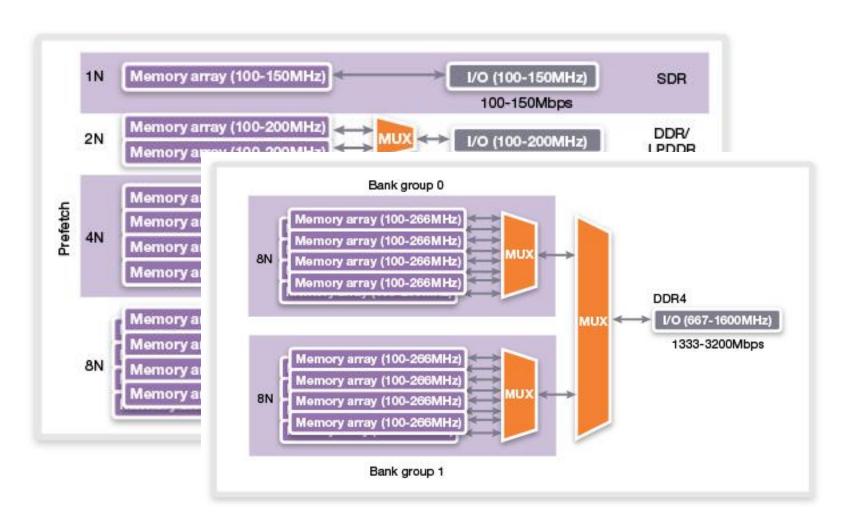


Figure 1. Simplified Block Diagram of 2n-Prefetch READ

Figure 2. Simplified Block Diagram of 2n-Prefetch WRITE

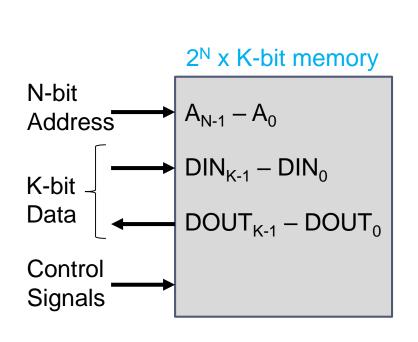
#### Other SDRAM Architectures- Cont.

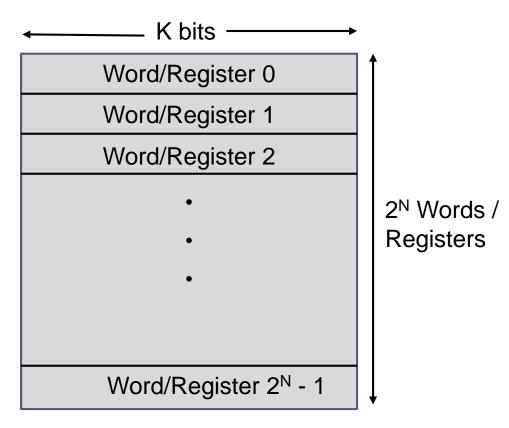


### **Memory Synthesis**

- Approaches:
  - Random logic using flip-flops or latches
  - Register files in data paths
  - RAM standard components
  - RAM compilers
- Computer "register files" are often just multi-port RAMs
  - ARM CPU: 32-bit registers R0-R15 => 16 x 32 RAM
  - MIPS CPU: 32-bit registers R0-R31 => 32 x 32 RAM
- Communications systems often use dual-port RAMs as transmit/receive buffers
  - FIFO (first-in, first-out RAM)

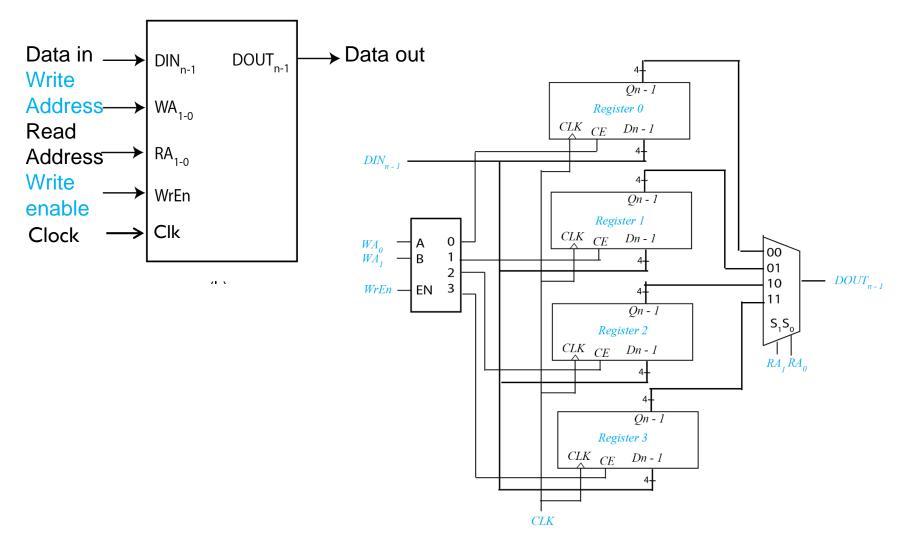
# Basic memory/register array





```
-- 2<sup>N</sup> x K-bit memory VHDL struture
signal MemArray: array (0 to 2**N – 1) of std_logic_vector(K-1 downto 0);
-- ARM register file is 16 32-bit registers
signal ARMregisterFile: array (0 to 15) of std_logic_vector(31 downto 0);
```

# Example: 4 x n-bit register file



#### Technology-independent RAM Models

-- N x K RAM is 2-dimensional array of N K-bit words library IEEE; **ADDR** use IEEE.std\_logic\_1164.all; DIN NxK use IEEE.std\_numeric\_std.all; RAM DOUT WR entity RAM is generic (K: integer:=8; -- number of bits per word -- number of address bits; N = 2^W W: integer:=8); port ( in std\_logic; -- active high write enable WR: ADDR: in std\_logic\_vector (W-1 downto 0); -- RAM address in std\_logic\_vector (K-1 downto 0); -- write data DIN: DOUT: out std\_logic\_vector (K-1 downto 0)); -- read data end entity RAM;

#### RAM Models in VHDL

```
architecture RAMBEHAVIOR of RAM is
  subtype WORD is std_logic_vector ( K-1 downto 0);
                                                 -- define size of WORD
  type MEMORY is array (0 to 2**A-1) of WORD;
                                                 -- define size of MEMORY
  signal RAM256: MEMORY;
                                                 -- RAM256 as signal of type MEMORY
begin
 process (WR, DIN, ADDR)
    variable RAM_ADDR_IN: natural range 0 to 2**W-1; -- translate address to integer
 begin
         RAM_ADDR_IN := to_integer(UNSIGNED(ADDR));
                                                           -- convert address to integer
         if (WR='1') then
                                                            -- write operation to RAM
               RAM256 (RAM ADDR IN) <= DIN :
         end if;
         DOUT <= RAM256 (RAM ADDR IN);
                                                            -- continuous read operation
  end process;
end architecture RAMBEHAVIOR;
               Multi-port RAM (two parallel outputs):
                 DOUT1 <= RAM256(to_integer(UNSIGNED(ADDR1));
                 DOUT2 <= RAM256(to_integer(UNSIGNED(ADDR2))
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```

#### Initialize RAM at start of simulation

```
process (WR, DIN, ADDR)
 variable RAM_ADDR_IN: natural range 0 to 2**W-1; -- to translate address to integer
 variable STARTUP: boolean := true;
                                                     -- temp variable for initialization
begin
  if (STARTUP = true) then -- for initialization of RAM during start of simulation
         RAM256 \le (0 \Rightarrow "00000101", --initializes first 4 locations in RAM
                       1 => "00110100", -- to specific values
                       2 => "00000110", -- all other locations in RAM are
                       3 = 00011000", -- initialized to all 0s
                       others => "00000000");
          DOUT <= "XXXXXXXXX"; -- force undefined logic values on RAM output
          STARTUP :=false; -- now this portion of process will only execute once
  else
      -- "Normal" RAM operations
```

#### RAM with bidirectional data bus

FIGURE 8-14: Block Diagram of Static RAM

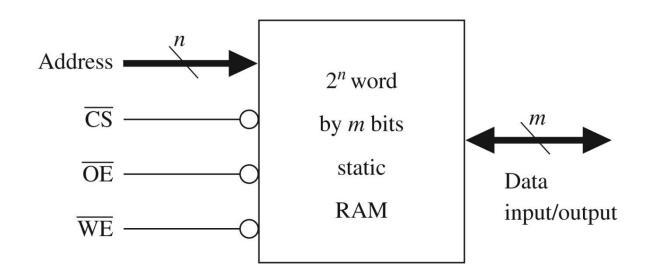


TABLE 8-7: Truth Table for Static RAM

CS	OE	WE	Mode	I/O pins
Н	Χ	X	not selected	high-Z
L	Н	Н	output disabled	high-Z
L	L	Н	read	data out
L	X	L	write	data in

# Single-port distributed RAM

```
library ieee;
use ieee.std logic 1164.all;
use ieee.std_logic_unsigned.all;
entity rams 04 is
                    clk: in std logic;
          port (
                                                                                    64x16
                    we : in std logic;
                                                                                     LUT
                    a: in std_logic_vector(5 downto 0);
                                                                             do
                    di: in std_logic_vector(15 downto 0);
                                                                                     RAM
                                                                             we
                     do : out std_logic_vector(15 downto 0));
end rams 04;
                                                                             clk
architecture syn of rams 04 is
          type ram_type is array (63 downto 0) of std_logic_vector (15 downto 0);
          signal RAM : ram type;
begin
          process (clk)
          begin
                    if (clk'event and clk = '1') then
                               if (we = '1') then
                                         RAM(conv_integer(a)) <= di;
                               end if:
                    end if:
          end process:
          do <= RAM(conv_integer(a));
end syn;
                                                        From Xilinx "Synthesis and Simulation
                                                        Design Guide"
```

#### FIGURE 6-18: Behavioral VHDL Code That Typically Infers LUT-Based Memory

```
library IEEE;
use IEEE.numeric_bit.all;
entity Memory is
  port(Address: in unsigned(6 downto 0);
      CLK, MemWrite: in bit;
      Data_In: in unsigned(31 downto 0);
      Data_Out: out unsigned(31 downto 0));
end Memory;
architecture Behavioral of Memory is
type RAM is array (0 to 127) of unsigned(31 downto 0);
signal DataMEM: RAM; -- no initial values
begin
  process(CLK)
  begin
    if CLK'event and CLK = '1' then
      if MemWrite = '1' then
        DataMEM(to_integer(Address)) <= Data_In; -- Synchronous Write</pre>
      end if:
    end if;
  end process;
  Data_Out <= DataMEM(to_integer(Address)); -- Asynchronous Read</pre>
end Behavioral:
```

#### **Block RAM inferred**

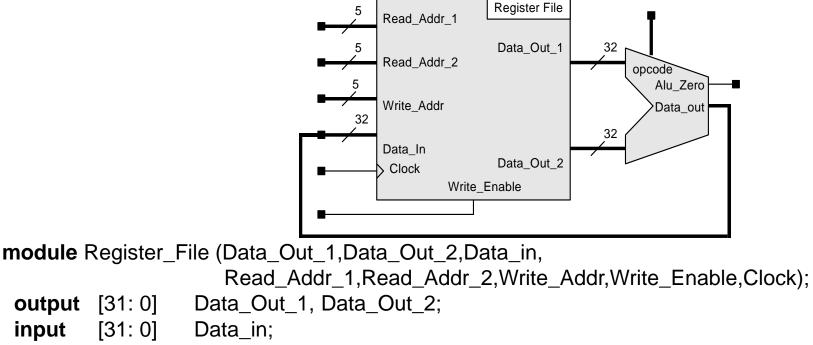
```
library ieee;
use ieee.std_logic_1164.all;
use ieee.std_logic_unsigned.all;
                                                                                   addr
entity rams 01 is
                                                                                   di
                       clk: in std logic;
           port (
                       we : in std logic;
                                                                                   do
                                                                                           64x16
                       en: in std logic;
                       addr: in std_logic_vector(5 downto 0);
                                                                                           BRAM
                       di: in std_logic_vector(15 downto 0);
                                                                                   we
                       do : out std_logic_vector(15 downto 0);
                                                                                   en
end rams_01;
                                                                                   clk
architecture syn of rams_01 is
           type ram_type is array (63 downto 0) of std_logic_vector (15 downto \overline{y},
           signal RAM: ram_type;
begin
            process (clk)
            begin
                       if clk'event and clk = '1' then
                              if en = '1' then
                                   if we = '1' then
                                          RAM(conv_integer(addr)) <= di;
                                   end if:
                                   do <= RAM(conv_integer(addr)); -- read-first operation</pre>
                              end if:
                       end if:
           end process;
end syn;
                                                                From Xilinx "Synthesis and Simulation
                                                                Design Guide"
```

#### FIGURE 6-19: Behavioral VHDL Code That Typically Infers Dedicated Memory

```
library IEEE;
use IEEE.numeric bit.all;
entity Memory is
  port(Address: in unsigned(6 downto 0);
       CLK, MemWrite: in bit;
       Data In: in unsigned(31 downto 0);
       Data Out: out unsigned(31 downto 0));
end Memory:
architecture Behavioral of Memory is
type RAM is array (0 to 127) of unsigned(31 downto 0);
signal DataMEM: RAM: -- no initial values
begin
  process(CLK)
  begin
    if CLK'event and CLK = '1' then
      if MemWrite = '1' then
        DataMEM(to integer(Address)) <= Data_In; -- Synchronous Write</pre>
      end if:
      Data Out <= DataMEM(to integer(Address)); -- Synchronous Read
    end if:
  end process:
end Behavioral:
```

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# Register File in Verilog



```
output [31: 0]
                  Data Out 1, Data Out 2:
         [31: 0]
 input
                  Data in;
 input
         [4: 0]
                  Read_Addr_1, Read_Addr_2, Write_Addr;
input
                  Write Enable, Clock:
         [31: 0] Reg File [31: 0]; // 32bit x32 word memory declaration
reg
 assign Data_Out_1 = Reg_File[Read_Addr_1];
 assign Data_Out_2 = Reg_File[Read_Addr_2];
 always @ (posedge Clock) begin
  if (Write_Enable) Reg_File [Write_Addr] <= Data_in;</pre>
 end
endmodule
```

### "Concept of Memory" in Verilog

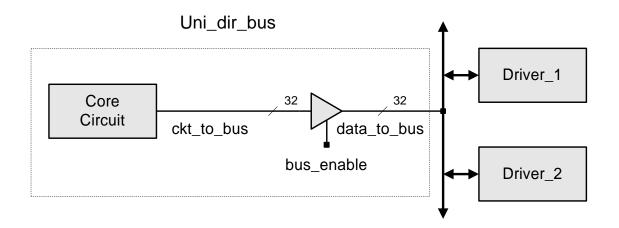
- Memory
  - Declaration an array of words
  - E.g. reg [31:0] data\_out; // one 32-bit word
     reg [31:0] Reg\_file [31:0]; // 32x32 bit word memory
- Verilog does not support 2-dimensional array
  - However, a word in a Verilog memory can be addressed directly
     E.g., Reg\_file [12]
  - A cell bit in a word can also be addressed indirectly by first loading the word into a buffer register then addressing the bit of the word

```
➤ E.g. Data_out = Reg_file [12];
Data_out [1:0]
```

 Decoder are synthesized automatically by synthesis tool in Reg\_file[] to decode the address which locates a specific register

#### **Bus Interface**

#### Unidirectional Bus

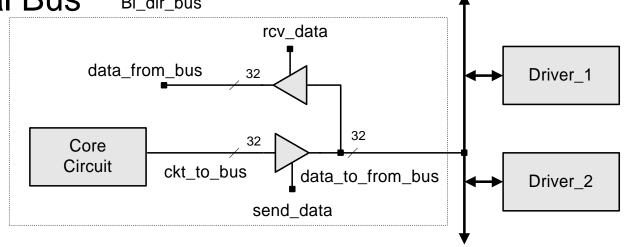


Michael D. Ciletti, Advanced digital design with the Verilog HDL.

#### Bus Interface

**Bidirectional Bus** 





```
module Bi_dir_bus (data_to_from_bus, send_data, rcv_data);
inout
        [31: 0] data_to_from_bus;
Input
                send_data, rcv_data;
wire
        [31: 0] ckt_to_bus;
        [31: 0] data_to_from_bus, data_from_bus;
wire
assign data_from_bus = (rcv_data)? data_to_from_bus: 32'bz;
assign data_to_from_bus = (send_data)? ckt_to_bus: data_to_from_bus;
// Behavior using data_from_bus and generating
// ckt_to_bus goes here
endmodule
```